

## CLAIMS

1. A structure for checking an integrated electronic device comprising:  
an oxide layer to be measured located above a body of doped semiconductor material and arranged in a position adjacent to a gate region of polycrystalline semiconductor material, said oxide layer having a first area;  
an oxide test region of the same material as said oxide layer and having the same thickness and the same electrical characteristics as said oxide layer; and  
a polycrystalline region of the same material as said gate region, having the same thickness and the same electrical characteristics as said gate region, and positioned adjacent to the oxide test region, said oxide test region having a second area greater than the first area.
2. A structure according to claim 1 wherein said polycrystalline region extends along a closed line.
3. A structure according to claim 2 wherein said closed line delimits an area with dimensions greater than  $50 \times 50 \mu\text{m}^2$ .
4. The structure according to claim 1 wherein said polycrystalline region laterally surrounds and delimits said oxide test region.
5. A structure for checking an integrated electronic device, comprising:  
a doped semiconductor material body;  
a gate region of polycrystalline semiconductor material;  
an oxide layer having a thickness to be determined, located above the semiconductor material body, arranged in a position adjacent to the gate region, and having a first area; and  
a test region positioned on the semiconductor material body, the test region including an oxide test region of a same material as the oxide layer and having a thickness

that is equal to the thickness of the oxide layer, the oxide test region having a second area that is greater than the first area and sufficiently large to be measured in a non-destructive manner by an ellipsometer.

6. The structure of claim 5 wherein the test region further includes a polycrystalline region that completely surrounds the oxide test region.

7. The test structure of claim 6 wherein the polycrystalline region extends along a closed line.

8. The test structure of claim 5 wherein the second area has dimensions greater than or equal to  $50 \times 50 \mu\text{m}^2$ .